

Organic Semiconductors for Thin Film Transistors

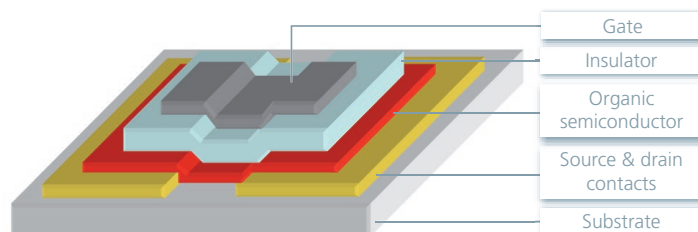
Example application areas for printable thin film transistors



- **Sensors:** transistors as part of circuits to enable these applications
- **Circuits (digital and analogue):** logic gates, amplifiers, circuitry for sensor applications
- **Displays:** select and drive transistors for controlling pixel operation
- Solution processed transistors enable wider printed electronics applications to be envisaged through integration with existing printed devices. These include wearable devices optionally on flexible/curved substrates (example concepts shown left)

General properties of organic semiconductor materials:

- Soluble in typical organic solvents (such as xylene) for solution processing (e.g. inkjet or slot die coating)
- Low temperature processing compatible (<120° C), therefore inherently suitable for devices on plastic substrates such as commonly used PEN or PET
- Post printing annealing processes are not required for high mobility devices → simple process to integrate with other organic electronic devices



Example test cell device on plastic in a top gate configuration. Lithographically defined electrodes to 5µm channel length resolution

Performance features and material design aspects:

- Mobility as high as 2.5 cm²/Vs. On/off current ratios >10⁵ on plastic substrates
- Suitable for use with either gold or silver source and drain contacts
- Low voltage device platform developed for ≤10 V operation
- Example performance summary chart of one material is shown below.

OSC material: Example technical specifications performance

Average saturation mobility (cm ² /Vs) at 10 µm	1.0 – 1.5 [bottom gate] 2.0 – 2.5 [top gate]
On/off current ratio	10 ⁵
Phase property	Amorphous
Sub-threshold slope (V/decade)	0.6 (L=10µm, BG)

All device data taken from a top gate, bottom contact architecture on plastic films with gold source and drain contacts

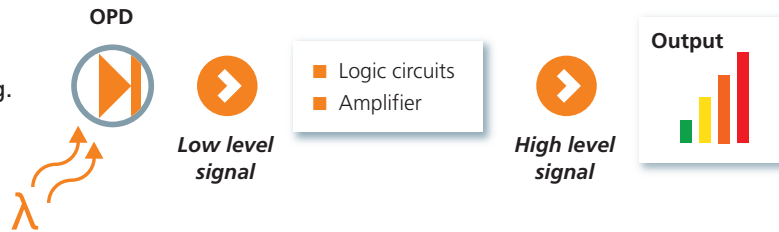
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Application example: Printed OTFT circuits for integrated systems

Input signal:

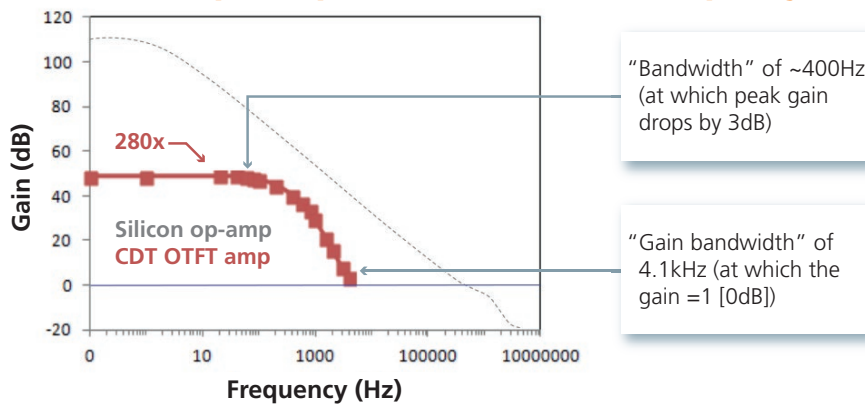
OPD as detector element in optical sensor system e.g.

- Biosensor
- Proximity sensor



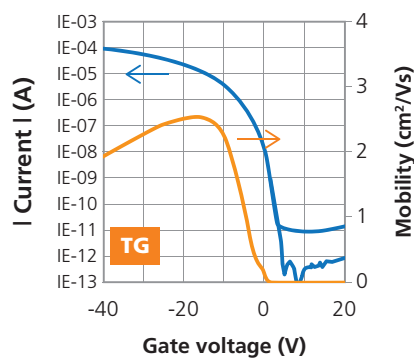
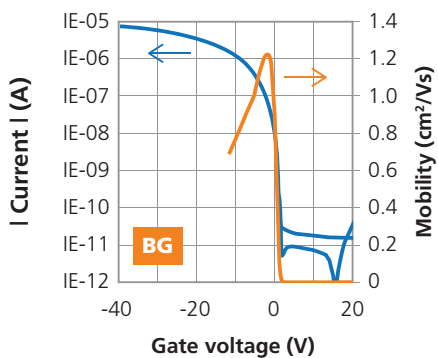
Output signal:
Increased voltage or current output

OTFT amplifier performance: Gain vs frequency

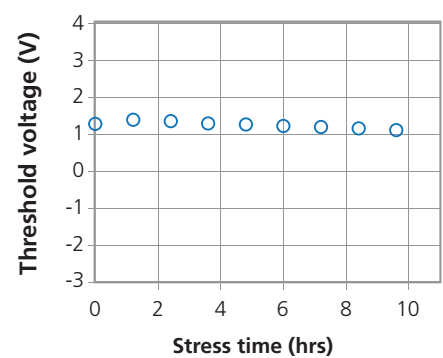


Printed OTFT device example data: Bottom gate (BG) and Top gate (TG) structures

Transfer characteristics



Threshold voltage stability



- Excellent mobility as high as 1 cm²/Vs and 2.5 cm²/Vs can be obtained at BG and TG structures, respectively
- Dielectric layer for BG is fabricated by using our original insulator material in PGMEA
- Threshold voltage shift extrapolated as a function of stress time is taken from transistors as a function of constant gate bias. Devices were subject to a constant gate bias of -20V for 9.6hours, measured periodically every 1.2 hours
- Inkjet and other printing methods can be applied due to the high solubility of OSC for common solvents and its amorphous nature.